

Schottky Diode

DSB15IM45IB

preliminary

 $V_{RRM} = 45 V$

 $I_{FAV} = 15 A$

 $V_F = 0.55 V$

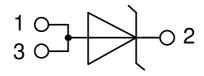
High Performance Schottky Diode Low Loss and Soft Recovery Single Diode

Part number

DSB15IM45IB



Backside: cathode



Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package: TO-262 (I2Pak)

- Industry standard outline
- RoHS compliant
- Epoxy meets UL 94V-0

Disclaimer Notice

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preliminary

Schottky				1	Ratings			
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blockir	ng voltage	$T_{VJ} = 25^{\circ}C$			45	V	
V _{RRM}	max. repetitive reverse blocking vo	oltage	$T_{VJ} = 25^{\circ}C$			45	V	
IR	reverse current, drain current	$V_R = 45 \text{ V}$	$T_{VJ} = 25^{\circ}C$			5	mA	
		$V_R = 45 V$	$T_{VJ} = 100$ °C			50	mΑ	
V _F	forward voltage drop	I _F = 15 A	$T_{VJ} = 25^{\circ}C$			0.59	٧	
		$I_F = 30 \text{ A}$				0.83	٧	
		I _F = 15 A	T _{VJ} = 125°C			0.55	V	
		$I_F = 30 A$				0.80	٧	
I _{FAV}	average forward current	T _C = 130°C	T _{vJ} = 150°C			15	Α	
		rectangular d = 0.5						
V _{F0}	threshold voltage $T_{v,l} = 150$ °C				0.31	٧		
r _F	slope resistance					15.5	mΩ	
R _{thJC}	thermal resistance junction to case	9				1.75	K/W	
R _{thCH}	thermal resistance case to heatsin	k			0.5		K/W	
P _{tot}	total power dissipation		$T_C = 25^{\circ}C$			70	W	
I _{FSM}	max. forward surge current	$t = 10 \text{ ms}$; (50 Hz), sine; $V_R = 0 \text{ V}$	$T_{VJ} = 45^{\circ}C$			340	Α	
CJ	junction capacitance	$V_R = 5V f = 1 MHz$	$T_{VJ} = 25^{\circ}C$		497		pF	

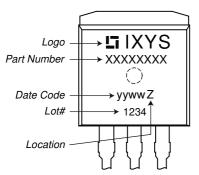


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Package	Package TO-262 (I2Pak)			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit	
I _{RMS}	RMS current	per terminal			35	Α	
T _{VJ}	virtual junction temperature		-55	5	150	°C	
T _{op}	operation temperature		-55	5	125	°C	
T _{stg}	storage temperature		-55	5	150	°C	
Weight				1.5		g	
F _c	mounting force with clip		20)	60	N	

Product Marking



Part description

D = Diode

S = Schottky Diode

B = ultra low VF

15 = Current Rating [A]

IM = Single Diode

45 = Reverse Voltage [V]

IB = TO-262 (I2Pak) (3)

Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	DSB15IM45IB	DSB15IM45IB	Tube	50	502322

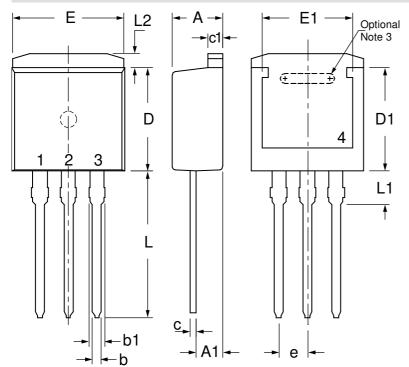
Equivalent Circuits for Simulation			* on die level	$T_{VJ} = 150^{\circ}C$
$I \rightarrow V_0$)—[R_o	Schottky		
V _{0 max}	threshold voltage	0.31		V
R _{0 max}	slope resistance *	12.4		mΩ



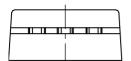


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Outlines TO-262 (I2Pak)



MYZ	INCHES		MILLIMETERS		
2114	MIN	MAX	MIN	MAX	
Α	160،	190،	4.06	4.83	
A1	.080	.110	2.03	2.79	
b	.025	.035	0.64	0.88	
b1	.025	.039	1.14	1.40	
С	.018	.025	0.46	0.64	
с1	.045	.055	1.14	1.40	
D	.340	.380	8,64	9,65	
D1	.270	.290	6.86	7.37	
Ε	.380	.405	9.65	10.29	
E1	.245	.320	6.22	8.13	
е	.100 BSC		2.54 BSC		
L	.500	.560	12.70	14.22	
L1	.100	.125	2.54	3.18	
L2	،040	.055	1.02	1,40	



NOTE:

- 1. This drawing will meet all dimensions requirement of JEDEC outline TO-262 AA.
- 2. All metal surface are matte pure tin plated except trimmed area.
- 3. Inter locking slot depends upon frame type.

